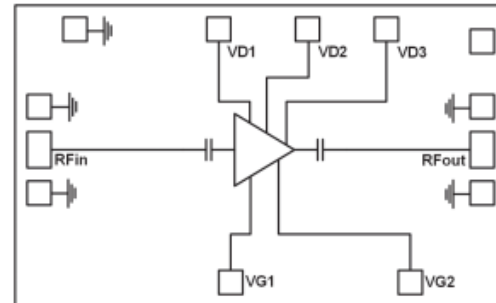


Features

- Frequency: 24-34GHz
- Gain: 27dB
- P1dB: +22.5dBm
- Psat: +23dBm
- Power supply: +5.0V, -0.65V@270mA
- Die Size: 2000 x 1000 μ m

Typical Applications

- Test Instrumentation
- Microwave Radio & VSAT
- Military & Space
- Telecom Infrastructure
- Fiber Optics

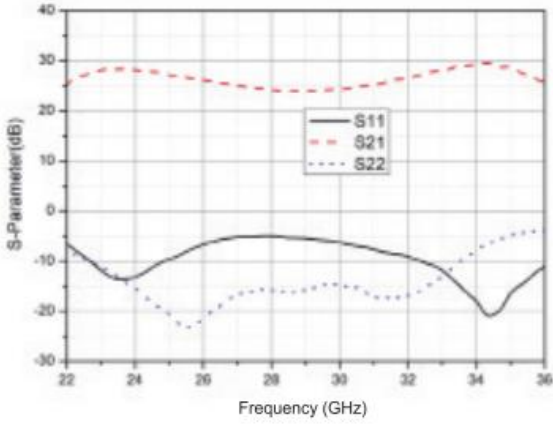
Functional Block Diagram

Electrical Specifications

TA = +25°C, Vdd = +5.0V, Vgg = -0.65V

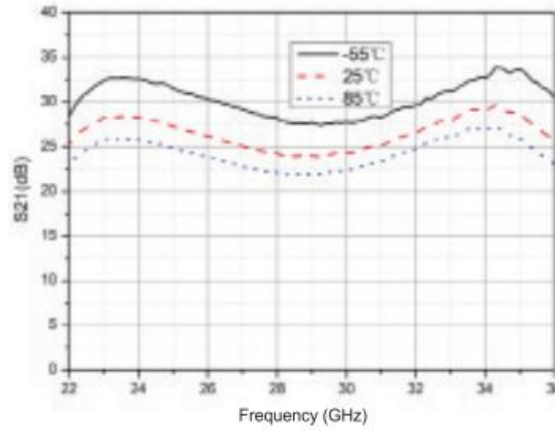
Parameters	Min.	Typ.	Max.	Units
Frequency	24-34			GHz
Gain		27		dB
P1dB		22.5		dBm
Input Return Loss		7		dB
Output Return Loss		7		dB
Operating Current		270		mA



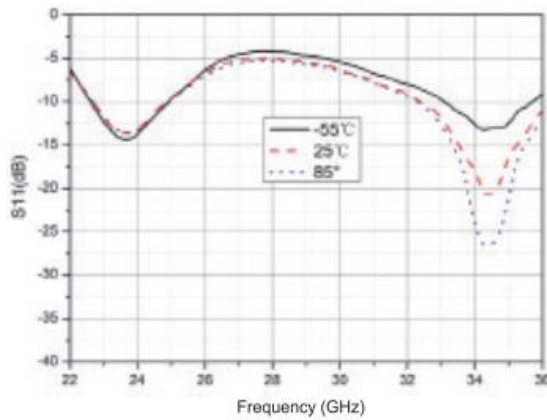
S-par vs. Frequency



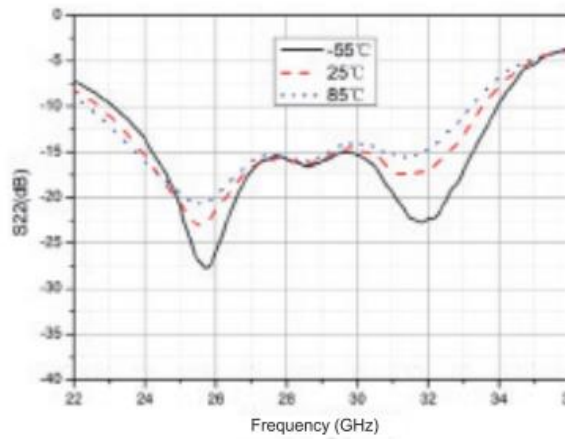
Gain vs. Frequency



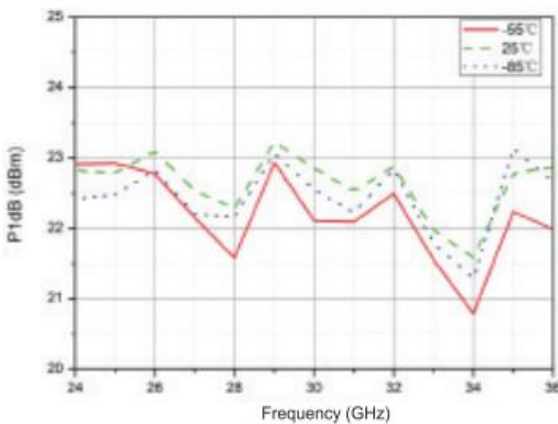
Input Return Loss vs. Frequency



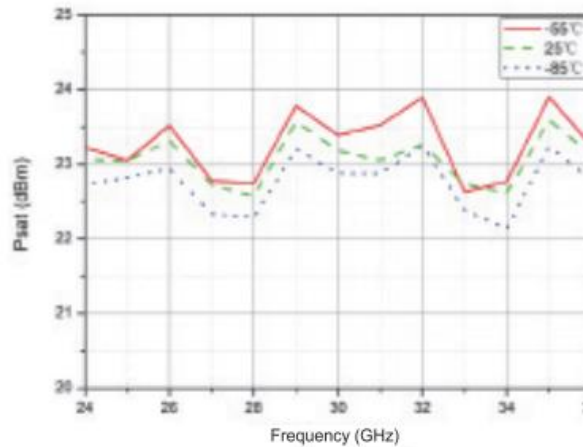
Output Return Loss vs. Frequency



P1dB vs. Frequency



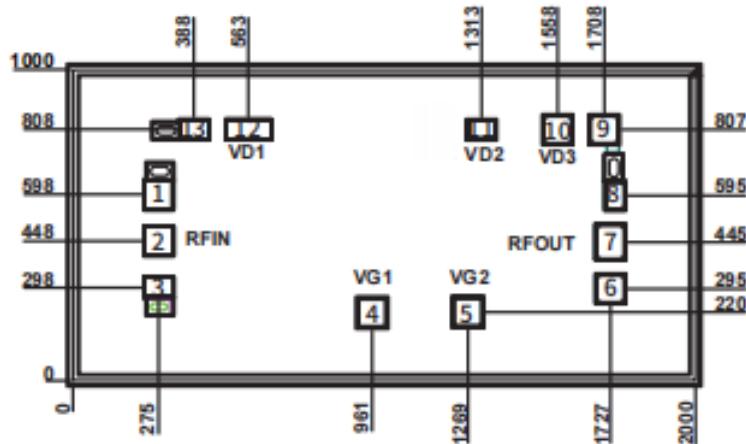
Psat vs. Frequency





Outline Drawing:

All Dimensions in um

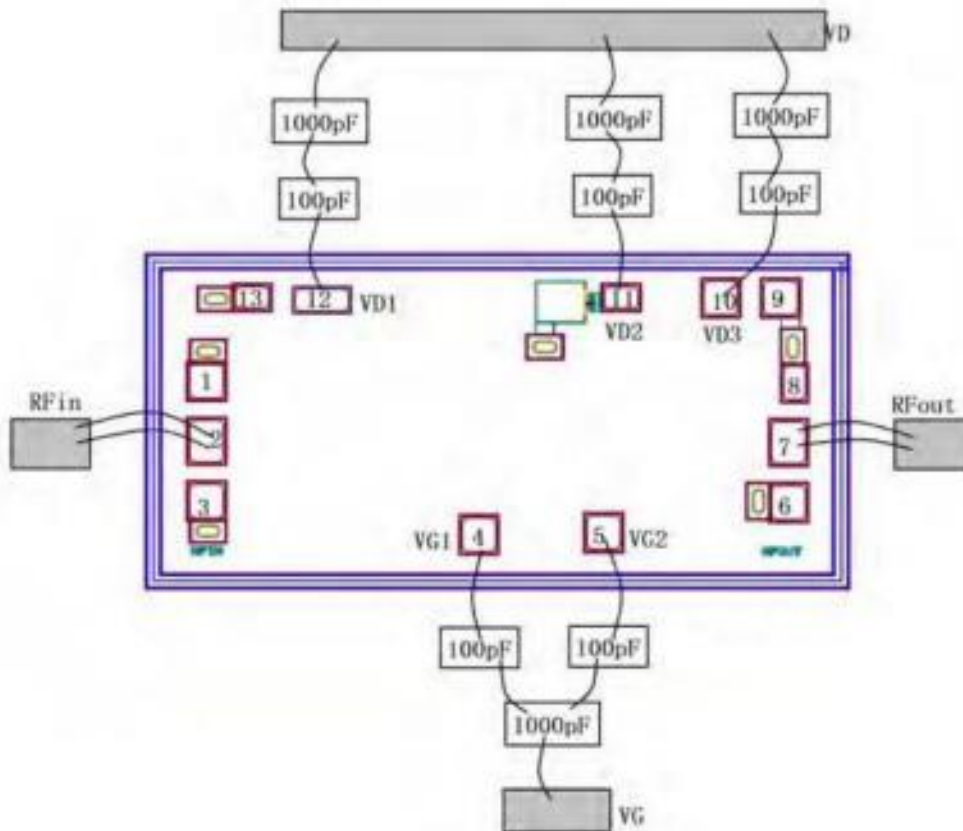


Pad Description

PAD	Function	Description
1,3,6,8,9,13	GND	Die bottom must be connected to RF/DC ground
2	RF IN	RF signal input terminal, external 50-ohm system required
7	RF OUT	RF signal output terminal, external 50-ohm system required
10,11,12	Vd	Amplifier power supply, external 100pF capacitor required
4,5	Vg	Amplifier gate power supply, external 100pF capacitor required



Assembly Drawing



Notes:

1. Die thickness: 100um
2. Typical bond pad is 100*100 μm²
3. Bond pad metalization: Gold
4. Backside metalization: Gold
5. Backside of the die (GND)
6. No connection required for unlabeled bond pads

Maximum Ratings:

1. Supply voltage: +6V
2. RF input power: +15dBm
3. Operating temperature: -55°C to +85°C
4. Storage temperature: -65°C to +150°C